Central™ Semiconductor Corp.

PROCESS CPD06

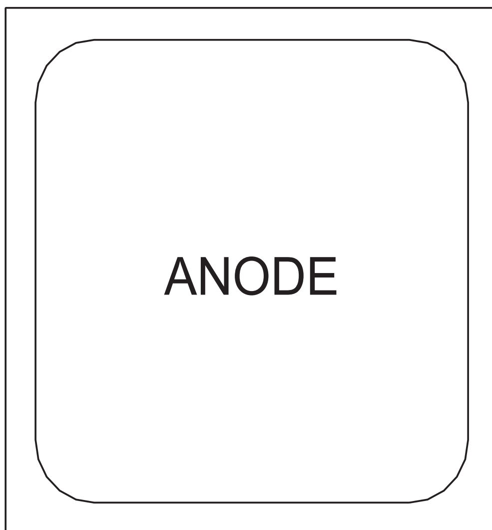
General Purpose Rectifier

3 Amp Glass Passivated Rectifier Chip

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	87 x 87 MILS
Die Thickness	10.4 MILS
Anode Bonding Pad Area	69.5 x 69.5 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER

1,490

PRINCIPAL DEVICE TYPES

1N5400 thru 1N5408
1N5550 thru 1N5554
1N5624 thru 1N5627
CMR3-02 Series

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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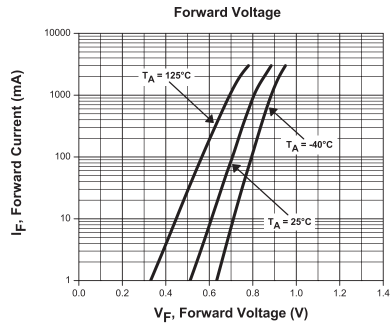
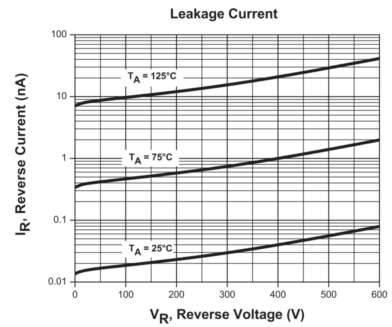
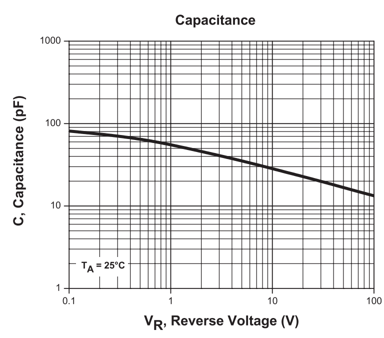
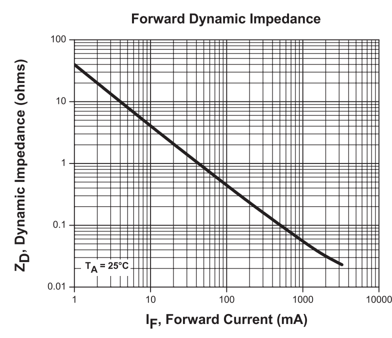
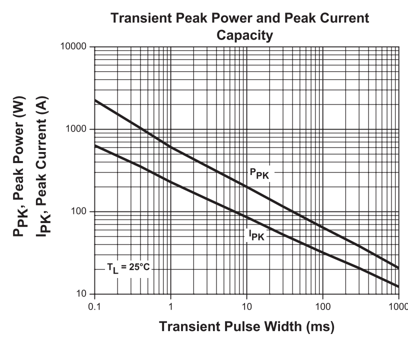
Typical Electrical Characteristics

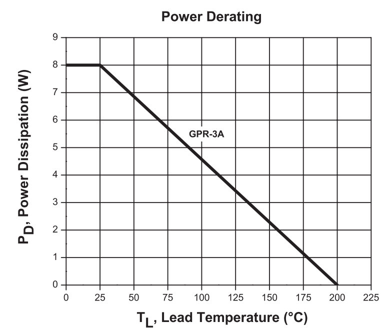












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